Silicon Carbide (SiC) Schottky Diode - EliteSiC, 20 A, 1200 V, D1, TO-247-2L

FFSH20120A

Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

Features

- Max Junction Temperature 175°C

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.



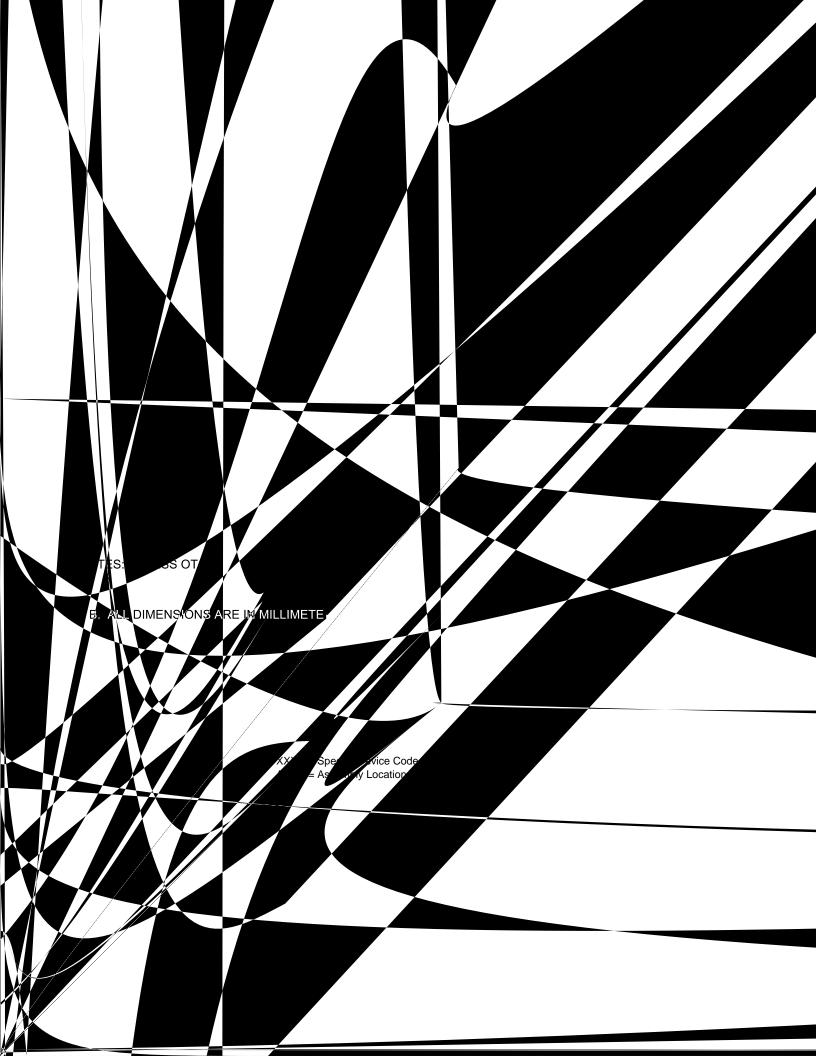
Schottky Diode

TO-247-2LD

CASE 340CL

MARKING DIAGRAM





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